

Features: (typical values)

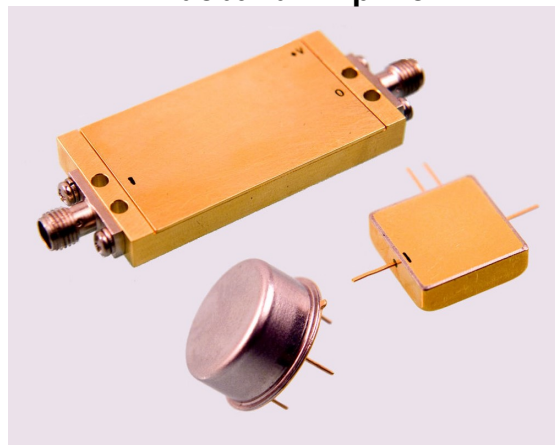
- Very high IP3 +38 dBm.
- High P1dB 28.0 dBm.
- NF 6.0 dB.
- Units to be conductive epoxy sealed
- No external components required

Maximum Ratings

Storage Temperature -62°C to +125°C
 DC Voltage +15 volts
 RF Input Power +15.0 dBm.
 Case Temperature +95°C

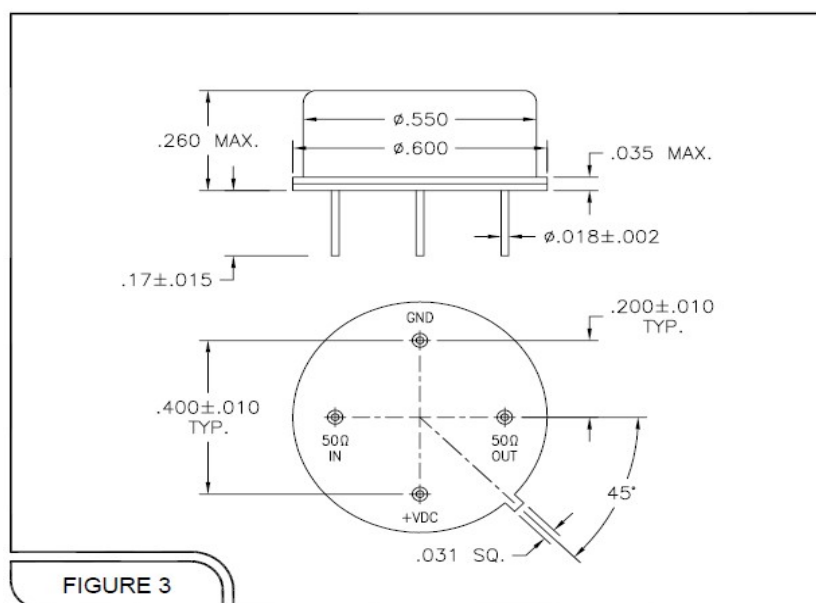
Specifications (Referenced to 50 ohms)

10-1000 MHz Wideband Amplifier



Parameter	Typical Conditions	Min Value	Max Value	Units
Frequency		10	1000	MHz.
Gain	13.0	12.0		dB.
Gain Flatness	±0.25		±0.75	dB.
Pout @ 1dB Comp.	10-500 MHz 500-1000 MHz	+28.0 +26.5	+25.5 +25.0	dBm.
NF	6.0		9.0	dB.
Reverse Isolation	17.0		15.0	dB.
IP ₃ /IP ₂ (two-tone)	38/45			dBm.
HIP2 (2 nd harm.)	50.0			dBm.
VSWR In/Out	1.7:1		2.0:1	
Supply Required	+12/195		+12/210	v/mA.

Min. and max. values are from -55°C to +85°C



FUNCTIONAL BLOCK DIAGRAM

